

INCHANGE Semiconductor

isc Product Specification

isc Silicon NPN Power Transistors

BDT81F/83F/85F/87F

DESCRIPTION

- DC Current Gain $-h_{FE} = 40(\text{Min})@ I_C = 5A$
- Collector-Emitter Sustaining Voltage-
: $V_{CEO(\text{SUS})} = 60V(\text{Min})$ - BDT81F; $80V(\text{Min})$ - BDT83F;
 $100V(\text{Min})$ - BDT85F; $120V(\text{Min})$ - BDT87F
- Complement to Type BDT82F/84F/86F/88F

APPLICATIONS

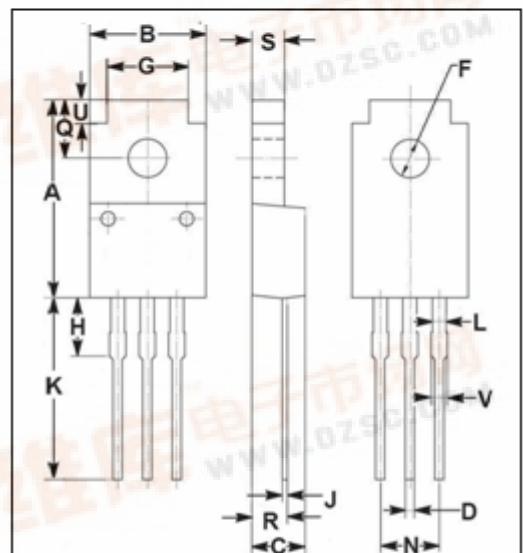
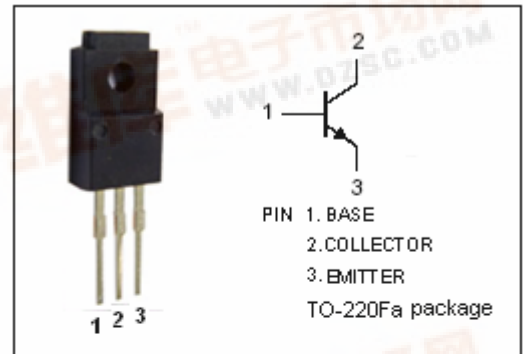
- Designed for use in audio output stages and general amplifier and switching applications

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	BDT81F	60
		BDT83F	80
		BDT85F	100
		BDT87F	120
V_{CEO}	Collector-Emitter Voltage	BDT81F	60
		BDT83F	80
		BDT85F	100
		BDT87F	120
V_{EBO}	Emitter-Base Voltage	7	V
I_C	Collector Current-Continuous	15	A
I_{CM}	Collector Current-Peak	20	A
I_B	Base Current	4	A
P_C	Collector Power Dissipation $T_C=25^\circ\text{C}$	36	W
T_j	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-65~150	$^\circ\text{C}$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance, Junction to Case	6	$^\circ\text{C/W}$



DIM	mm	
	MIN	MAX
A	16.85	17.15
B	9.90	10.10
C	4.35	4.65
D	0.75	0.80
F	3.20	3.40
G	6.90	7.10
H	5.15	5.45
J	0.45	0.75
K	13.35	13.65
L	1.10	1.30
N	4.98	5.18
Q	4.85	5.15
R	2.95	3.25
S	2.70	2.90
U	1.75	2.05
V	1.30	1.50

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ELECTRICAL CHARACTERISTICS

 $T_C=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	BDT81F	$I_C=30\text{mA}; I_B=0$	60			V
		BDT83F		80			
		BDT85F		100			
		BDT87F		120			
$V_{CE(sat)-1}$	Collector-Emitter Saturation Voltage		$I_C=5\text{A}; I_B=0.5\text{A}$			1.0	V
$V_{CE(sat)-2}$	Collector-Emitter Saturation Voltage		$I_C=7\text{A}; I_B=0.7\text{A}$			1.6	V
$V_{BE(on)}$	Base-Emitter On Voltage		$I_C=5\text{A}; V_{CE}=4\text{V}$			1.5	V
I_{CES}	Collector Cutoff Current		$V_{CE}=0.8V_{CB0max}; V_{BE}=0$			1	mA
I_{CBO}	Collector Cutoff Current		$V_{CB}=V_{CB0max}; I_E=0$			0.2	mA
I_{EBO}	Emitter Cutoff Current		$V_{EB}=7\text{V}; I_C=0$			0.1	mA
h_{FE-1}	DC Current Gain		$I_C=50\text{mA}; V_{CE}=10\text{V}$	40			
h_{FE-2}	DC Current Gain		$I_C=5\text{A}; V_{CE}=4\text{V}$	40			
f_T	Current-Gain—Bandwidth Product		$I_C=0.5\text{A}; V_{CE}=10\text{V}$		10		MHz

Switching Times

t_{on}	Turn-On Time	$I_C=7\text{A}; I_{B1}=-I_{B2}=0.7\text{A}$			1	μs
t_{off}	Turn-Off Time				2	μs